September 25, 2025
ROHM Co., Ltd.
Infineon Technologies AG

ROHM and Infineon collaborate on silicon carbide power electronics packages to enhance flexibility for customers

ROHM and Infineon Technologies AG have signed a Memorandum of Understanding to collaborate on packages for silicon carbide (SiC) power semiconductors used in applications such as on-board chargers, photovoltaics, energy storage systems, and AI data centers. Specifically, the partners aim to enable each other as second sources of selected packages for SiC power devices, a move which will increase design and procurement flexibility for their customers. In the future, customers will be able to source devices with compatible housings from both ROHM and Infineon. The collaboration will ensure seamless compatibility and interchangeability to match specific customer needs.

"We are excited about working with ROHM to further accelerate the establishment of SiC power devices," said Dr. Peter Wawer, Division President Green Industrial Power at Infineon. "Our collaboration will provide customers with a wider range of options and greater flexibility in their design and procurement processes, enabling them to develop more energy-efficient applications that will further drive decarbonization."

"ROHM is committed to providing customers with the best possible solutions. Our collaboration with Infineon constitutes a significant step towards the realization of this goal, since it broadens the portfolio of solutions," said Dr. Kazuhide Ino, Member of the Board, Managing Executive Officer, in charge of Power Devices Business at ROHM. "By working together, we can drive innovation, reduce complexity, and increase customer satisfaction, ultimately shaping the future of the power electronics industry."

Dr. Peter Wawer, Division President Green Industrial Power at Infineon (left)
and Dr. Kazuhide Ino, Member of the Board and Managing Executive Officer at ROHM

As part of the agreement, ROHM will adopt Infineon’s innovative top-side cooling platform for SiC, including TOLT, D-DPAK, Q-DPAK, Q-DPAK dual, and H-DPAK packages. Infineon's top-side cooling platform offers several benefits, including a standardized height of 2.3 mm for all packages. This facilitates designs and reduces system costs for cooling, while also enabling better board space utilization and up to two times more power density.

At the same time, Infineon will take on ROHM’s DOT-247 package with SiC half-bridge configuration to develop a compatible package. That will expand Infineon’s recently announced Double TO-247 IGBT portfolio to include SiC half-bridge solutions. ROHM's advanced DOT-247 delivers higher power density and reduces assembly effort compared to standard discrete packages. Featuring a unique structure that integrates two TO-247 packages, it enables to reduce thermal resistance by approximately 15 percent and inductance by 50 percent compared to the TO-247. The advantages bring 2.3 times higher power density than the TO-247.

ROHM and Infineon plan to expand their collaboration in the future to include other packages with both silicon and wide-bandgap power technologies such as SiC and gallium nitride (GaN). This will further strengthen the relationship between the two companies and provide customers with an even broader range of solutions and sourcing options.

Semiconductors based on SiC have improved the performance of high-power applications by switching electricity even more efficiently, enabling high reliability and robustness under extreme conditions, while allowing for even smaller designs. Using ROHM’s and Infineon’s SiC products, customers can develop energy-efficient solutions and increase power density for applications such as electric vehicle charging, renewable energy systems and AI data centers.

About ROHM

ROHM, a leading semiconductor and electronic component manufacturer, was established in 1958. From the automotive and industrial equipment markets to the consumer and communication sectors, ROHM supplies ICs, discretes, and electronic components featuring superior quality and reliability through a global sales and development network. Our strengths in the analog and power markets allow us to propose optimized solutions for entire systems that combine peripheral components (i.e., transistors, diodes, resistors) with the latest SiC power devices as well as drive ICs that maximize their performance.

Further information is available at https://www.rohm.com

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About Infineon

Infineon Technologies AG is a global semiconductor leader in power systems and IoT. Infineon drives decarbonization and digitalization with its products and solutions. The company has around 58,060 employees worldwide and generated revenue of about €15 billion in the 2024 fiscal year (ending 30 September). Infineon is listed on the Frankfurt Stock Exchange (ticker symbol: IFX) and in the USA on the OTCQX International over-the-counter market (ticker symbol: IFNNY).

Further information is available at www.infineon.com

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